



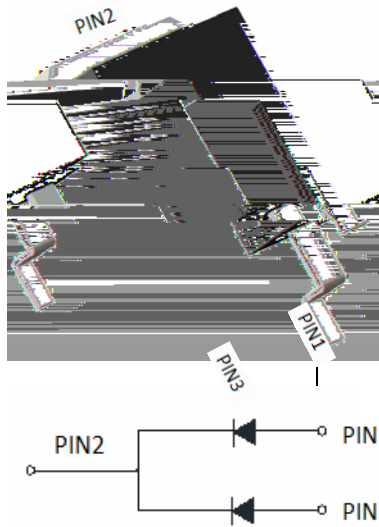
MBRB1020CT THRU MBRB1060CT

RoHS
COMPLIANT

Schottky Diodes

Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guaranteed JESD22-B102



- Polarity: As marked

Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER				SYMBOL	UNIT	MBRB1020CT	MBRB1035CT	MBRB1045CT	MBRB1050CT	MBRB1060CT
Device marking code						MBRB1020CT	MBRB1035CT	MBRB1045CT	MBRB1050CT	MBRB1060CT
Repetitive Peak Reverse Voltage				VRRM	V	20	17	15	12	10
Current Squared Time @1ms≤t<8.3ms Tj=25				I ² t	A ² s			41		
Storage Temperature				T _{stg}				-55 ~ +150		
Junction Temperature				T _j			-55 ~ +125		-55 ~ +150	
■										
Maximum instantaneous forward voltage drop per diode	V _{FM}	V	IFM=5.0A			0.55			0.75	
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	V _{RM} =V _{RRM} T _a =25				0.2			
	I _{RRM2}		V _{RM} =V _{RRM} T _a =100			20				
Note1:Pulse test:300uS pulse width,1% duty cycle Note2:Pulse test:pulse width 40mS										
a						1 / 4			± 3%	
S-B684 Rev.1.1,02-Aug-23				Yangzhou	Yangjie Electronic	Technology	Co., Ltd.	www.21yangjie.com		



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■Thermal Characteristics $T_a=25$ Unless otherwise specified

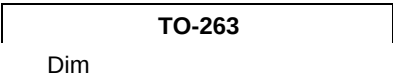
PARAMETER		SYMBOL	UNIT	MBRB1020CT	MBRB1035CT	MBRB1040CT	MBRB1050CT	MBRB1060CT
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	$^{\circ}W$					
				2.0				

■P

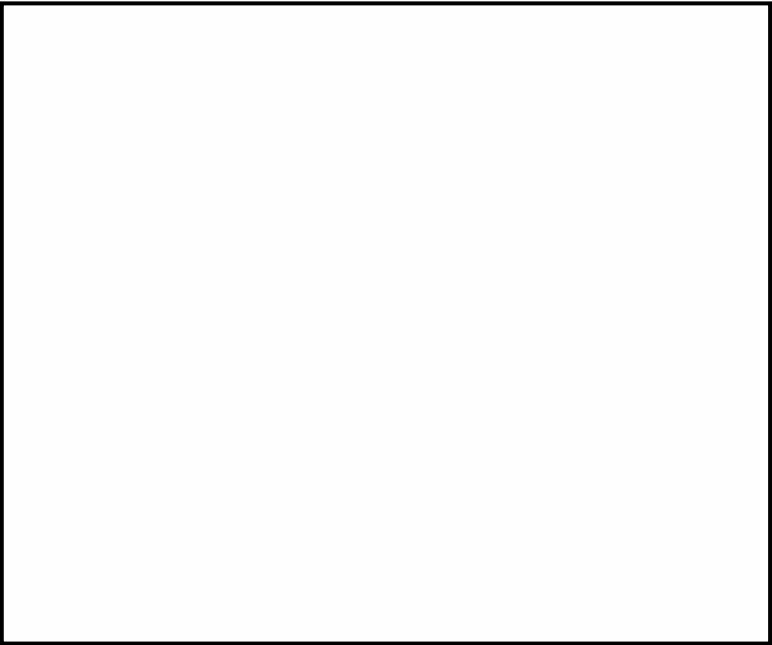


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■Outline Dimensions



■Suggested Pad Layout



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